

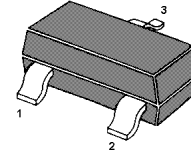
MMBTSC3531-AH

NPN Silicon Epitaxial Planar Transistor

low frequency power amp,converter electronic
governor applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	3	A
Power Dissipation	P_{tot}	0.6	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 50\text{ mA}$	h_{FE} h_{FE} h_{FE}	120	-	240	-
Current Gain Group Y		200	-	400	-
G		30	-	-	-
at $V_{CE} = 2\text{ V}$, $I_C = 1\text{ A}$					
Collector Base Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Base Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	-	-	1.2	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$	f_T	-	180	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	15	-	pF

